

DESCRIPTION:

With high ability to withstand the shock loading of large current, BTB06-800SW series triacs provide high dv/dt rate with strong resistance to electromagnetic interference. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.



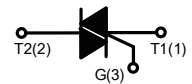
TO-251



TO-220A



TO-220F


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
V_{DRM}/V_{RRM}	600/800	V

ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	°C
Operating junction temperature range		T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	600/800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	600/800	V
RMS on-state current	TO-220A(Ins)/ TO-220F(Ins)/ TO-251 ($T_c=100^\circ\text{C}$)	$I_{T(RMS)}$	6	A
	TO-220A(Non-Ins) ($T_c=105^\circ\text{C}$)			
Non repetitive surge peak on-state current (full cycle, $F=50\text{Hz}$)		I_{TSM}	60	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	18	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)	I - II - III	di/dt	50	A/ μs
	IV		10	

Peak gate current	I_{GM}	2	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value		Unit
				C	B	
I_{GT}	$V_D=12V R_L=30\Omega$	I - II - III	MAX	25	50	mA
		IV		50	70	
V_{GT}		ALL	MAX	1.5		V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3K\Omega$	ALL	MIN	0.2		V
I_L	$I_G=1.2I_{GT}$	I - III - IV	MAX	50	70	mA
		II		60	80	
I_H	$I_{TM}=0.2A$		MAX	40	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	200	500	V/ μs

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=8.5A t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	μA
I_{RRM}		$T_j=125^\circ\text{C}$	1	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	2.9	$^\circ\text{C/W}$
		TO-220F(Ins)		
		TO-220A(Non-Ins) 2.3	2.7	
		TO-251		

FIG.1: Maximum power dissipation versus RMS on-state current

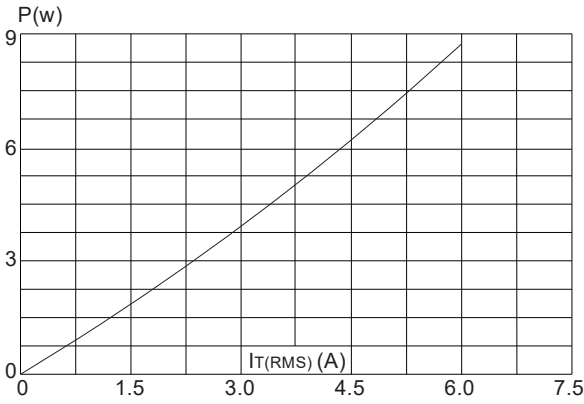


FIG.2: RMS on-state current versus case temperature

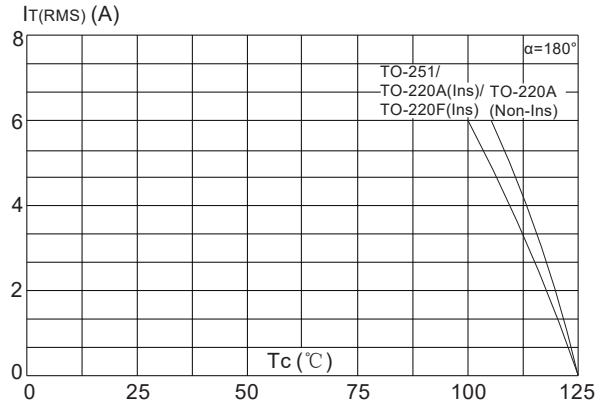


FIG.3: Surge peak on-state current versus number of cycles

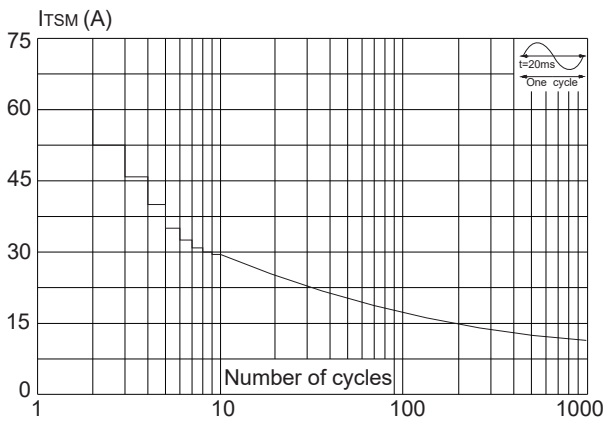


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t (I - II - III: $di/dt < 50A/\mu s$; IV: $di/dt < 10A/\mu s$)

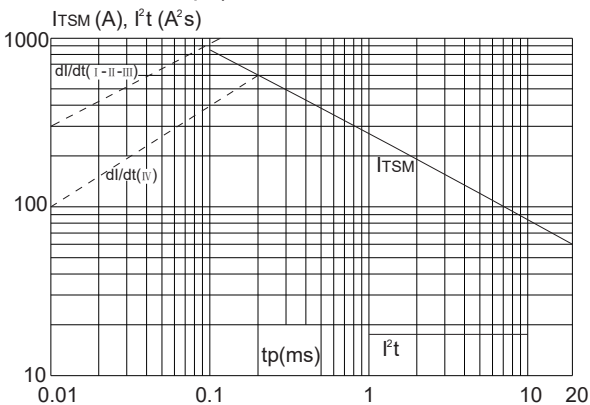


FIG.4: On-state characteristics (maximum values)

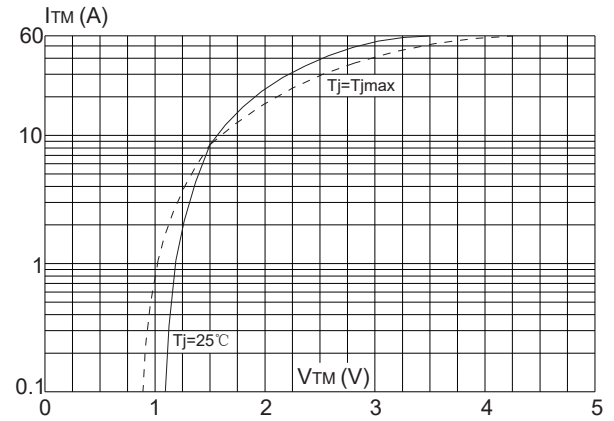


FIG.6: Relative variations of gate trigger current versus junction temperature

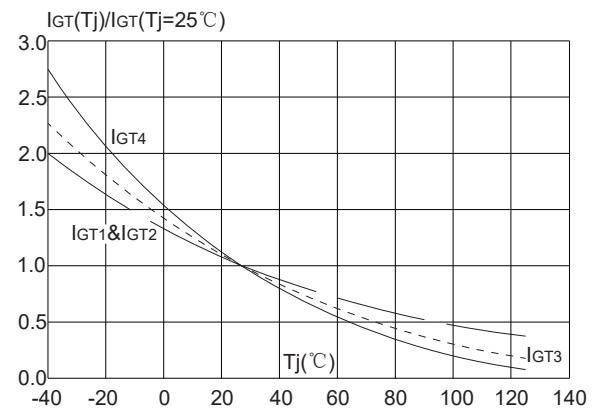


FIG.7: Relative variations of holding current versus junction temperature

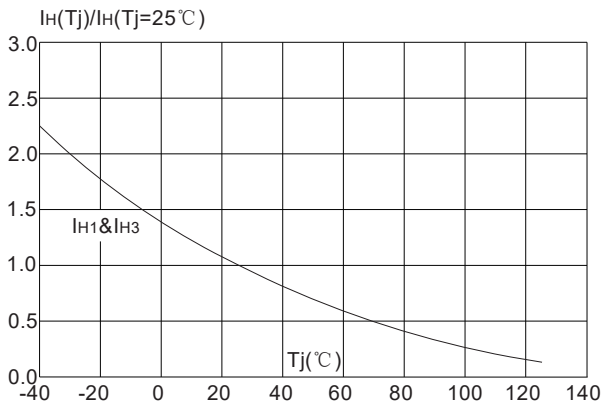


FIG.8: Relative variations of latching current versus junction temperature

